

# HN7G02FU

Power Management Switch Application, Inverter Circuit Application, Driver Circuit Application and Interface Circuit Application.

Q1 (transistor): RN2110 Equivalent  
 Q2 (MOS-FET): 2SK1830 Equivalent

### Q1 (Transistor) Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EB0</sub>	-5	V
Collector current	I <sub>C</sub>	-100	mA

### Q2 (MOS-FET) Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V <sub>DS</sub>	20	V
Gate-source voltage	V <sub>GSS</sub>	10	V
DC drain current	I <sub>D</sub>	50	mA

### Q1, Q2 Common Ratings (Ta = 25°C)

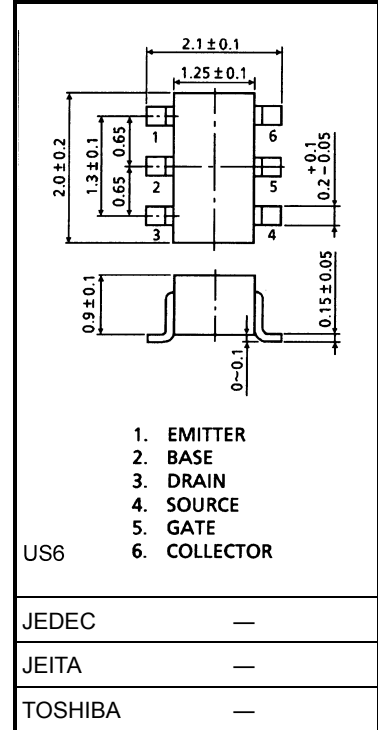
Characteristics	Symbol	Rating	Unit
Collector power dissipation	P <sub>C</sub> (Note 1)	200	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

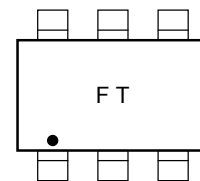
Note 1: Total rating

Unit: mm

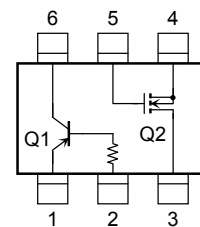


Weight: g (typ.)

### Marking



### Equivalent Circuit (top view)



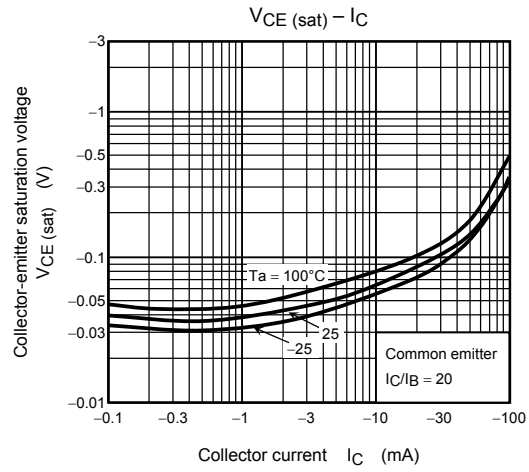
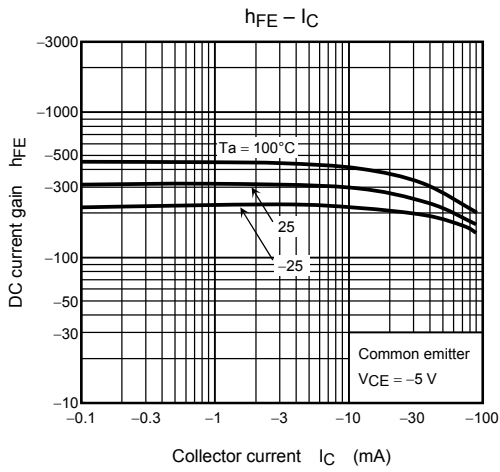
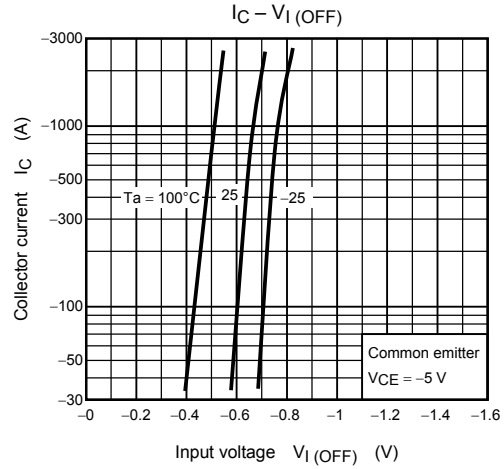
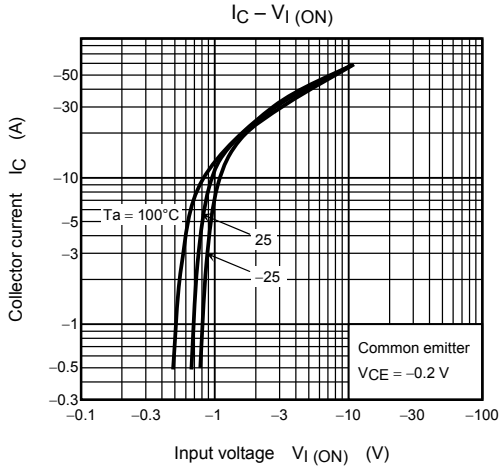
## Q1 (Transistor) Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = -50\text{ V}, I_E = 0$	—	—	-100	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-100	nA
DC current gain	$h_{FE}$	$V_{CE} = -5\text{ V}, I_C = -1\text{ mA}$	120	—	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 5\text{ mA}, I_B = -0.25\text{ mA}$	—	-0.1	-0.3	V
Input resistor	R1	—	3.29	4.7	6.11	kΩ

## Q2 (MOS-FET) Electrical Characteristics (Ta = 25°C)

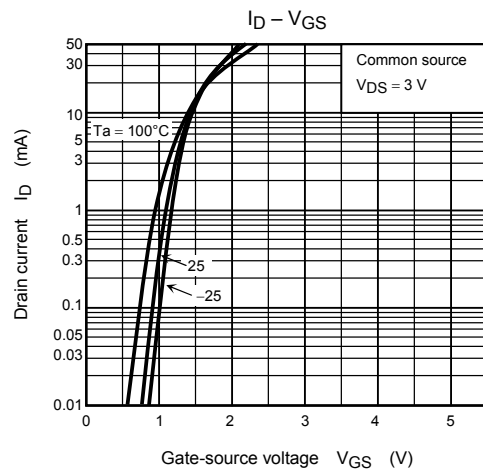
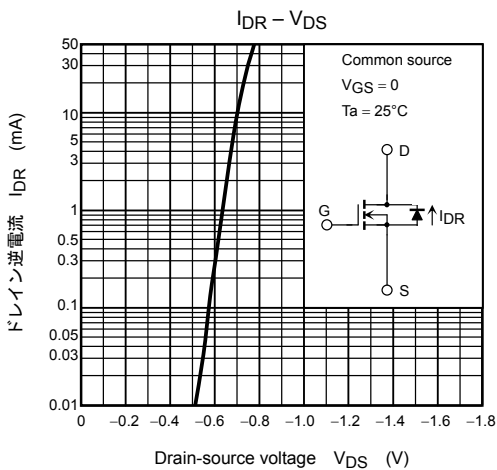
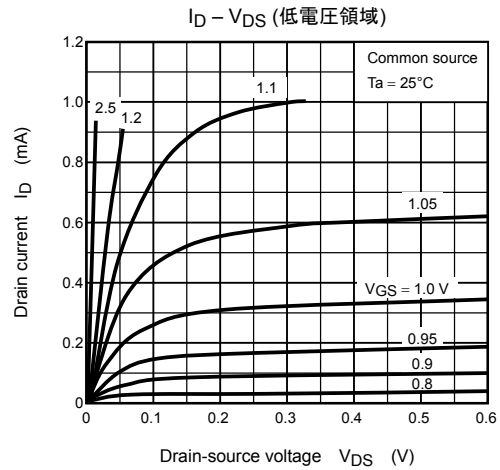
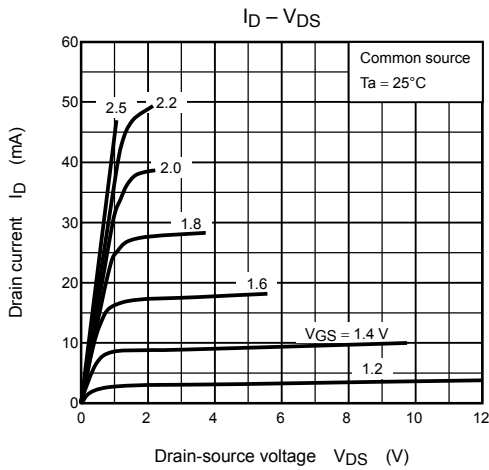
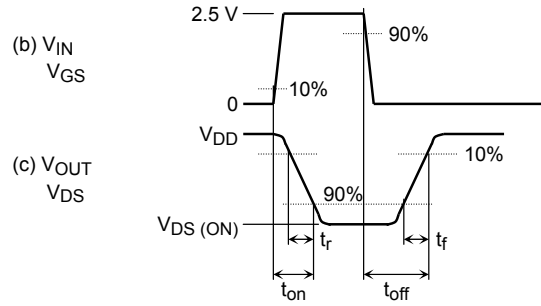
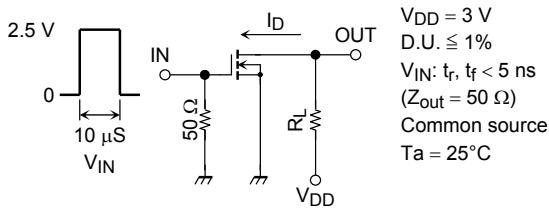
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = 10\text{ V}, V_{DS} = 0$	—	—	1	μA
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 100\text{ μA}, V_{GS} = 0$	20	—	—	V
Drain cut-off current	$I_{DSS}$	$V_{DS} = 20\text{ V}, V_{GS} = 0$	—	—	1	μA
Gate threshold voltage	$V_{th}$	$V_{DS} = 3\text{ V}, I_D = 0.1\text{ mA}$	0.5	—	1.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3\text{ V}, I_D = 10\text{ mA}$	20	—	—	mS
Drain-source ON resistance	$R_{DS(ON)}$	$I_D = 10\text{ mA}, V_{GS} = 2.5\text{ V}$	—	20	40	Ω

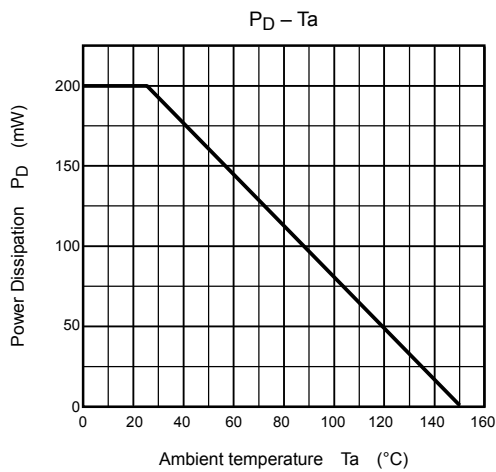
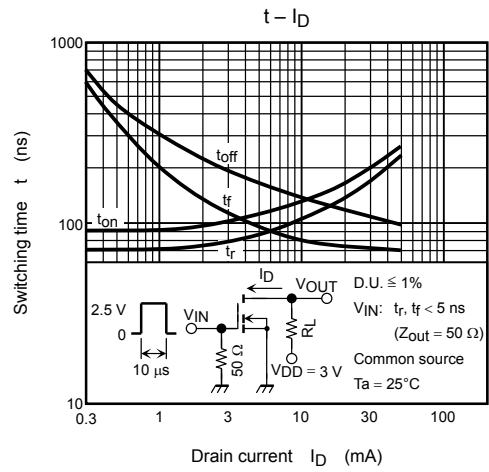
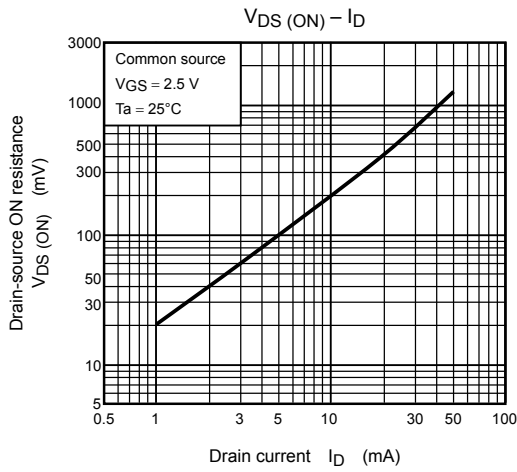
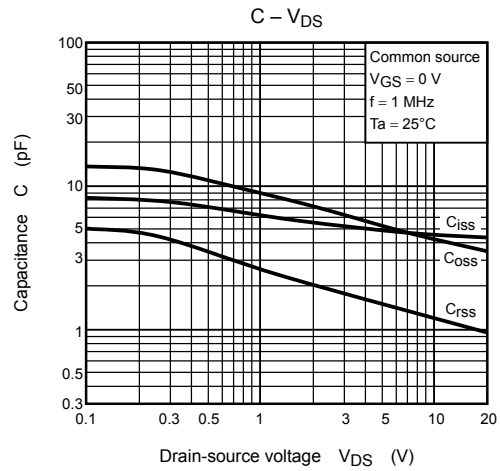
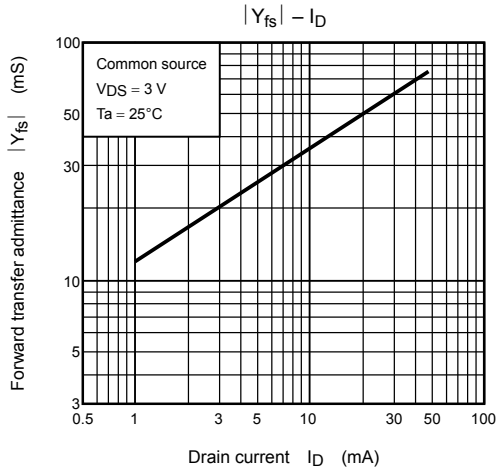
Q1 (Transistor)



## Q2 (MOS-FET)

(a) Switching time test circuit





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20070701-EN GENERAL

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